

First Call for Papers

The 12th International Symposium on Power Semiconductor Devices & ICs

May 22-25, 2000
Toulouse, France

Sponsor : IEEE Electron Devices Society

Co-Sponsor : The Institute of Electrical Engineers of Japan

The Twelfth International Symposium on Power Semiconductor Devices & ICs (ISPSD'2000) provides a forum for technical discussion in all areas of **Power Semiconductor Devices** and **Power ICs** and their **Applications**. Areas of interest include, but are not restricted to the following:

- Materials and Processes:** Crystal Growth, Doping, Lifetime Control, Passivation, Thick Film Metallization, Semiconductor Materials, Characterisation,
- CAD and Simulation** : Process, Device, Circuit, Thermal, Electrothermal, Electromechanical Aspects,
- Devices** : Device Physics, Modelling, Characterization, Reliability, Fast Switching, High Frequency Power, Discrete and Integrated Power,
- Monolithic and Hybrid Power Integrations** : Technology, Isolation Techniques, Design, Smart Power IC's, High Voltage IC's, Hybrid, Modules,
- Packaging** : Thermal Management, Novel Techniques, Stress and Reliability, Electrothermal Cycling,
- Applications** : All discrete and integrated power areas, device design and optimization for specific application.

PAPER SUBMISSION

Prospective authors must submit 40 copies of a 500 word summary on A4 or US Letter size paper in English with one page of supporting materials, headed by title of the paper, author's names, affiliations, mailing address, phone and FAX numbers and Email address to the Technical Program Secretariat: Daurat Dominique, LAAS-CNRS, 7 Avenue du Colonel Roche – 31077 Toulouse Cedex 4 – France.

DEAD LINE FOR SUBMISSION OF SUMMARY is OCTOBER 15, 1999. Notices of acceptance will be sent to authors by December 22, 1999. The final manuscript, in English, will be required for the Proceedings no later than February 18, 2000.

Best Student Paper Award: Papers presented by students and based on their own work will be considered for the Best Student Paper Award IF THE ABSTRACT IS IDENTIFIED AS A STUDENT PAPER AT THE TIME OF SUBMISSION. The award presentation will be made at the 2000 ISPSD.

All questions or inquiries for further information regarding this symposium should be directed to the General Chairman: Charitat Georges and the Technical Chairman: Sénès Albert. You could also visit the web site <http://www.laas.fr/ISPSD2000>.

General Chairman

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